

IN THE CLAIMS

1. (Previously presented) A memory device for use with a memory controller, the memory device comprising:
 - a memory cell array adapted to store internal depth data of an object;
 - a compare circuit;
 - a line connecting the compare circuit to the memory cell array; and
 - a data modifying circuit distinct from the memory controller, the data modifying circuit including the compare circuit and being adapted to:
 - receive an activate command from the memory controller,
 - receive corresponding new external depth data of the object from the memory controller,
 - compare the new external depth data with the internal depth data,
 - transfer the external depth data, via the connecting line, into the memory cell array, depending on the result of the comparison,
 - if the external depth data is transferred, over-write the internal depth data in the memory cell array with the transferred external depth data, and
 - output to the memory controller a status signal within predetermined clock cycles from receipt of the activate command from the memory controller.
2. (Cancelled)
3. (Previously presented) The memory device of claim 1, further comprising:
 - a first control pin for receiving a first control signal originally from the memory controller; and
 - a control circuit for transmitting the external depth data to the memory cell array thereby bypassing the data modifying circuit depending on a state of the first control signal.
4. (Cancelled)
5. (Previously presented) The memory device of claim 3, wherein the status signal is output through the first control pin.

6. (Previously presented) The memory device of claim 1, wherein the data modifying circuit includes

a register for storing the received new external depth data, wherein the compare circuit is adapted to compare the stored new external depth data with the internal depth data, and adapted to write the external depth data, via the connecting line, into the memory cell array depending on the result of the comparison.

7. (Original) The memory device of claim 6, wherein the compare circuit is further adapted to write the external depth data in the memory cell array if the external depth data is smaller than the internal depth data.

8. (Original) The memory device of claim 6, wherein the compare circuit is further adapted to output a status signal to the memory controller.

9. (Original) The memory device of claim 6, further comprising:
a second control pin for receiving a second control signal from the memory controller,
wherein the compare circuit compares the internal depth data with the stored external depth data in units of X bits when the second control signal is in a non-active state, and in units of NX bits when the second control signal is in an active state.

10. (Currently amended) A memory device for use with a memory controller, the memory device comprising:

a memory cell array adapted to store internal depth data of an object;
a compare circuit;
a line connecting the compare circuit to the memory cell array; and
a data modifying circuit distinct from the memory controller, the data modifying circuit including the compare circuit and being adapted to:
receive corresponding new external depth data of the object from the memory controller,
compare the new external depth data with the internal depth data,
transfer the external depth data, via the connecting line, into the memory cell array, depending on the result of the comparison,

if the external depth data is transferred, over-write the internal depth data in the memory cell array with the transferred external depth data, and

output to the memory controller a status signal;

wherein if a control pin is in an inactive state, the compare circuit outputs to the memory controller:

a first status signal indicating that the lower X bits of the internal depth data have been ~~modified~~ over-written with the external depth data, and

a second status signal indicating that the upper X bits of the internal depth data have been ~~modified~~ over-written with the external depth data.

11. (Original) The memory device of claim 9, wherein

if the second control pin is in a non-active state, the compare circuit outputs to the memory controller a status signal indicating that NX bits of the internal depth data have been modified.

12. (Currently amended) A method of processing depth data of an object in a memory device controlled by a memory controller, the method comprising:

receiving external depth data of the object from the memory controller;

storing the received external depth data;

receiving a first control signal from the memory controller through a first control pin distinct from the memory controller;

determining a state of the first control signal;

if the state of the first control signal is determined to be inactive, writing the external depth data to a memory cell array within the memory device,

else if the state of the first control signal is determined to be active,

receiving the stored external depth data and corresponding internal depth data stored in the memory cell array at a compare circuit that is distinct from the memory controller and connected via a line to the memory cell array, comparing the received data,

writing from the compare circuit the external depth data over the corresponding internal depth data in the memory cell array by transferring the external depth data via the connected line, depending on the result of the comparison, and

outputting to the memory controller a status signal indicating that the internal depth data has been modified;

receiving a second control signal from the memory controller through a second control pin distinct from the memory controller;

determining a state of the second control signal; and

if the state of the second control signal is determined to be inactive, comparing the internal depth data with the stored external depth data in units of X bits,

elseif the state of the second control signal is determined to be active, comparing the internal depth data with the stored external depth data in units of NX bits,

wherein comparing the internal depth data with the stored external depth data in units of NX bits further includes

outputting to the memory controller a first status signal indicating that the lower X bits of the internal depth data have been ~~modified~~ over-written with the external depth data, and

outputting to the memory controller a second status signal indicating that the upper X bits of the internal depth data have been ~~modified~~ over-written with the external depth data.

13. (Cancelled)

14. (Previously presented) The method of claim 12, wherein writing the external depth data takes place if the comparison yields that the external depth data is smaller than the internal depth data.

15. (Previously presented) The method of claim 12, wherein writing the external depth data takes place if the comparison yields that the external depth data is larger than the internal depth data.

16-17. (Cancelled)

18. (Previously presented) The method of claim 12, wherein the first status signal is output through the first control pin, and the second status signal is output through the second control pin.

19. (Cancelled)

20. (Previously presented) The method of claim 12, wherein the status signal is output through one of the first and second control pins.

21-23. (Cancelled)

24. (Previously presented) The memory device of claim 1, further comprising a first control pin that directly connects the compare circuit to the memory controller.

25. (Previously presented) The memory device of claim 24, wherein the first control pin is adapted to receive a first control signal from the memory controller and to output a first status signal to the memory controller.

26. (Previously presented) The memory device of claim 25, further comprising a second control pin that directly connects the compare circuit to the memory controller.

27. (Previously presented) The memory device of claim 26, wherein the second control pin is adapted to receive a second control signal from the memory controller and to output a second status signal to the memory controller.

28-31. (Cancelled)

32. (Previously presented) A method for processing depth data of an object in a memory device controlled by a memory controller, the method comprising:

generating at least seven clock cycles;

receiving an activate command from the memory controller responsive to a first of the at least seven clock cycles;

receiving a depth-compare write command from the memory controller responsive to a third of the at least seven clock cycles;

receiving external depth data responsive to the third of the at least seven clock cycles, the external depth data indicating a distance between the object on a display screen and a viewer;

receiving at least one control signal from the memory controller responsive to the third of the at least seven clock cycles;

comparing the received external depth data with internal depth data stored in a memory cell array of the memory device, the comparing being completed before one of a sixth and a seventh of the seven clock cycles,

wherein at least one status signal is transmitted from the memory device to the memory controller, the at least one status signal indicating whether the internal depth data was replaced with the external depth data, the at least one status signal being transmitted responsive to a predetermined number of clock cycles.

33. (Previously presented) The method of claim 32, further comprising replacing the internal depth data with the external depth data if the external depth data is smaller than the internal depth data, the replacement occurring without modifying the external depth data.

34. (Previously presented) The method of claim 33, wherein the comparing and the replacing are completed before one of the sixth and the seventh of the seven clock cycles.

35. (Previously presented) The method of claim 34, wherein at least one status signal is transmitted from the memory device to the memory controller, the at least one status signal indicating whether the internal depth data was replaced with the external depth data, the at least one status signal being transmitted responsive to one of the sixth and the seventh of the seven clock cycles.

36. (New) The memory device of claim 6, wherein the compare circuit is further adapted to write the external depth data in the memory cell array if the external depth data is larger than the internal depth data.

37. (New) The memory device of claim 32, further comprising replacing the internal depth data with the external depth data if the external depth data is larger than the internal depth data, the replacement occurring without modifying the external depth data.

38. (New) The memory device of claim 10, wherein the compare circuit is adapted to over-write the internal depth data with the external depth data if the comparison yields that the external depth data is larger than the internal depth data.